



High Efficiency Thyristor

$V_{RRM} = 1200\text{ V}$

$I_{TAV} = 15\text{ A}$

$V_T = 1.35\text{ V}$

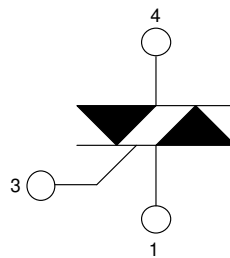
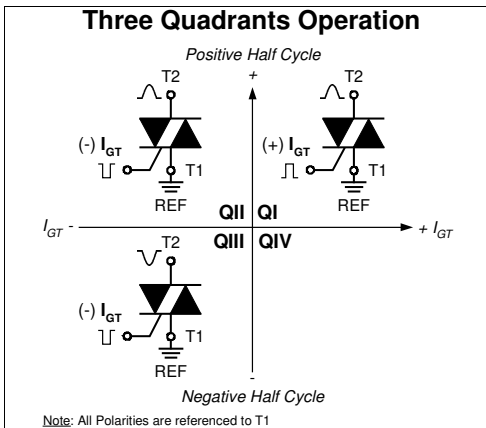
Three Quadrants operation: QI - QIII
1~ Triac

Part number

CLA30MT1200NPB



Backside: anode/cathode



Features / Advantages:

- Triac for line frequency
- Three Quadrants Operation - QI - QIII
- Planar passivated chip
- Long-term stability of blocking currents and voltages

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-220

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- High creepage distance between terminals

Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.

Rectifier			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1300	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V
I_{RD}	reverse current, drain current	$V_{R/D} = 1200\text{ V}$	$T_{VJ} = 25^{\circ}C$		10	μA
		$V_{R/D} = 1200\text{ V}$	$T_{VJ} = 125^{\circ}C$		1.5	mA
V_T	forward voltage drop	$I_T = 15\text{ A}$	$T_{VJ} = 25^{\circ}C$		1.35	V
		$I_T = 30\text{ A}$			1.68	V
		$I_T = 15\text{ A}$	$T_{VJ} = 125^{\circ}C$		1.35	V
		$I_T = 30\text{ A}$			1.79	V
I_{TAV}	average forward current	$T_C = 120^{\circ}C$	$T_{VJ} = 150^{\circ}C$		15	A
I_{RMS}	RMS forward current per phase	180° sine			33	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		0.89	V
r_T	slope resistance				30	m Ω
R_{thJC}	thermal resistance junction to case				0.95	K/W
R_{thCH}	thermal resistance case to heatsink			0.5		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		130	W
I_{TSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		170	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		185	A
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}C$		145	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		155	A
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		145	A ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		140	A ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}C$		105	A ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		100	A ² s
C_J	junction capacitance	$V_R = 400\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}C$		9	pF
P_{GM}	max. gate power dissipation	$t_p = 30\text{ }\mu s$	$T_C = 150^{\circ}C$		5	W
		$t_p = 300\text{ }\mu s$			1	W
P_{GAV}	average gate power dissipation				0.2	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 150^{\circ}C; f = 50\text{ Hz}$ repetitive, $I_T = 45\text{ A}$			150	A/ μs
		$t_p = 200\text{ }\mu s; di_G/dt = 0.3\text{ A}/\mu s;$ $I_G = 0.3\text{ A}; V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 15\text{ A}$			500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150^{\circ}C$		500	V/ μs
		$R_{GK} = \infty$; method 1 (linear voltage rise)				
V_{GT}	gate trigger voltage	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}C$		1.3	V
			$T_{VJ} = -40^{\circ}C$		1.6	V
I_{GT}	gate trigger current	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}C$		± 40	mA
			$T_{VJ} = -40^{\circ}C$		± 60	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150^{\circ}C$		0.2	V
I_{GD}	gate non-trigger current				± 1	mA
I_L	latching current	$t_p = 10\text{ }\mu s$	$T_{VJ} = 25^{\circ}C$		70	mA
		$I_G = 0.3\text{ A}; di_G/dt = 0.3\text{ A}/\mu s$				
I_H	holding current	$V_D = 6\text{ V}$ $R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		50	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$		2	μs
		$I_G = 0.3\text{ A}; di_G/dt = 0.3\text{ A}/\mu s$				
t_q	turn-off time	$V_R = 100\text{ V}; I_T = 15\text{ A}; V = \frac{2}{3} V_{DRM}$ $T_{VJ} = 125^{\circ}C$ $di/dt = 10\text{ A}/\mu s$ $dv/dt = 20\text{ V}/\mu s$ $t_p = 200\text{ }\mu s$			150	μs



Package TO-220			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			35	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		150	°C
Weight				2		g
M_D	mounting torque		0.4		0.6	Nm
F_C	mounting force with clip		20		60	N

Product Marking



Part description

- C = Thyristor (SCR)
- L = High Efficiency Thyristor
- A = (up to 1200V)
- 30 = Current Rating [A]
- MT = 1~ Triac
- 1200 = Reverse Voltage [V]
- N = Three Quadrants operation: QI - QIII
- PB = TO-220AB (3)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	CLA30MT1200NPB	CLA30MT1200NPB	Tube	50	517031

Similar Part	Package	Voltage class
CLA30MT1200NPZ	TO-263AB (D2Pak) (2HV)	1200

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}C$

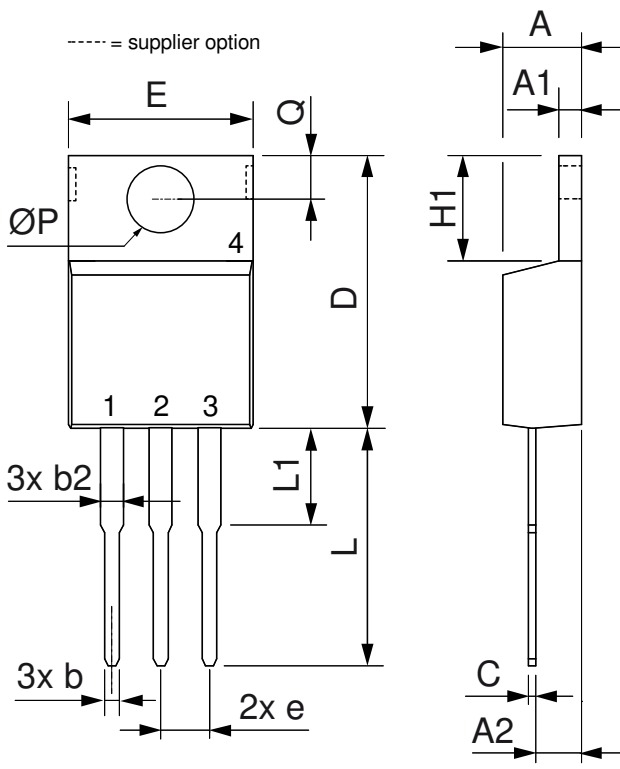


Thyristor

$V_{0\ max}$	threshold voltage	0.89	V
$R_{0\ max}$	slope resistance *	27	mΩ



Outlines TO-220



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
C	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
e	2.54	BSC	0.100	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125



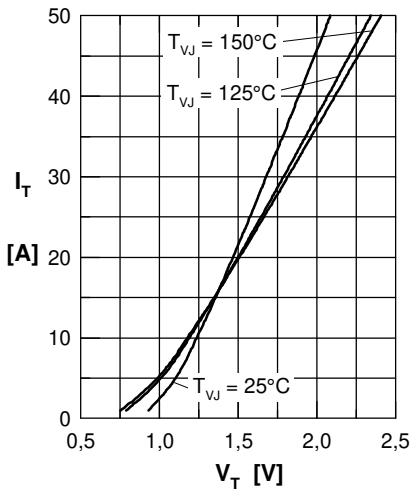
Thyristor


Fig. 1 Forward characteristics

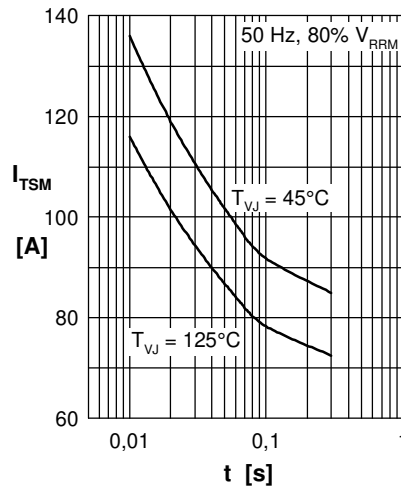


Fig. 2 Surge overload current

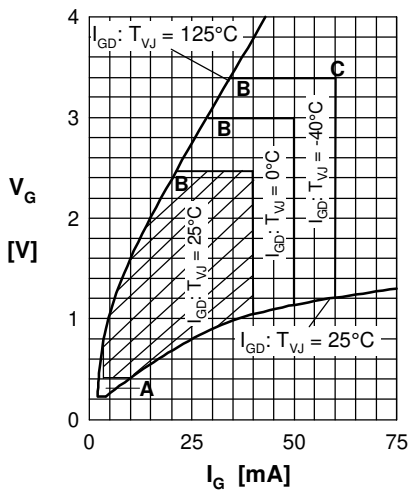

 Fig. 3 I^2t versus time (1-10 ms)


Fig. 4 Gate trigger characteristics



Fig. 5 Gate controlled delay time



Fig. 6 Max. forward current at case temperature

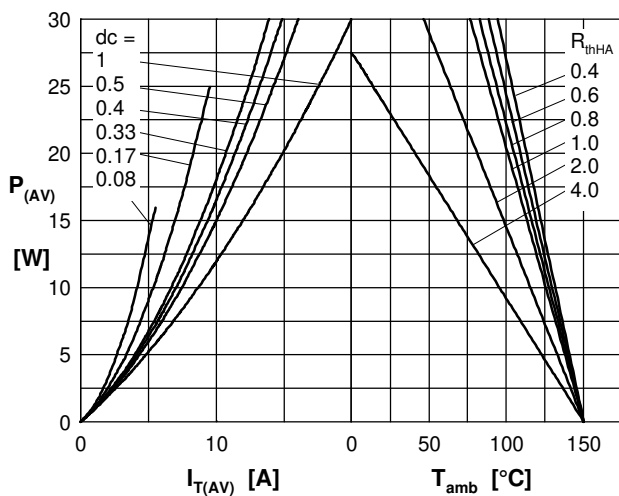
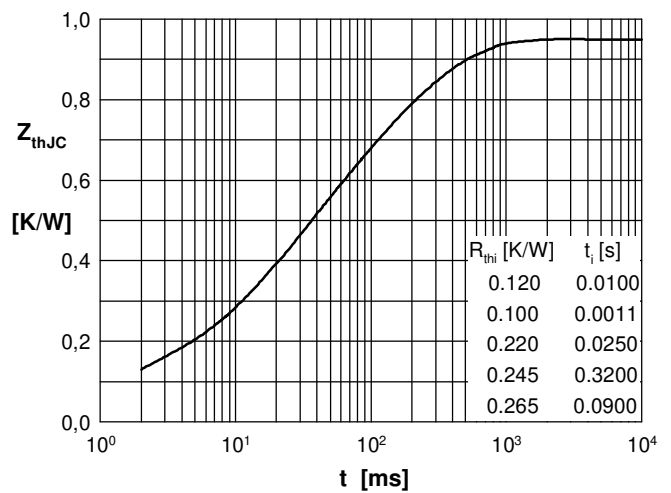

 Fig. 7a Power dissipation versus direct output current
 Fig. 7b and ambient temperature


Fig. 8 Transient thermal impedance